

P-Channel Enhancement Mode Power MOSFET

Description

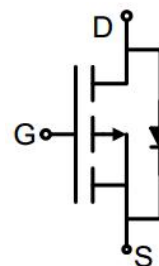
The GT600P15T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} -150V
- I_D (at $V_{GS} = -10V$) -45A
- $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 70m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-220

Ordering Information

Device	Package	Marking	Packaging
GT600P15T	TO-220	GT600P15	50pcs/Tube

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-150	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$ -45	A
		$T_C = 100^\circ\text{C}$ -28	
Pulsed Drain Current (note1)	I_{DM}	-180	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	185	W
Single pulse avalanche energy (note2)	E_{AS}	324	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	R_{thJC}	0.68	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-150	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -150V, V_{GS} = 0V$	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-2.0	-3.3	-4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -25A$	--	55	70	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -25A$	--	30	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = -75V,$ $f = 1.0MHz$	--	3950	--	pF
Output Capacitance	C_{oss}		--	250	--	
Reverse Transfer Capacitance	C_{rss}		--	5	--	
Total Gate Charge	Q_g	$V_{DD} = -75V,$ $I_D = -25A,$ $V_{GS} = -10V$	--	58	--	nC
Gate-Source Charge	Q_{gs}		--	25	--	
Gate-Drain Charge	Q_{gd}		--	6	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -75V,$ $I_D = -25A,$ $R_G = 1.6\Omega$	--	14	--	ns
Turn-on Rise Time	t_r		--	17	--	
Turn-off Delay Time	$t_{d(off)}$		--	48	--	
Turn-off Fall Time	t_f		--	16	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^{\circ}C$	--	--	-45	A
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}C, I_{SD} = -25A, V_{GS} = 0V$	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	$I_F = -25A, V_{GS} = 0V$ $di/dt = -100A/us$	--	98	--	nC
Reverse Recovery Time	T_{rr}		--	52	--	ns

Notes

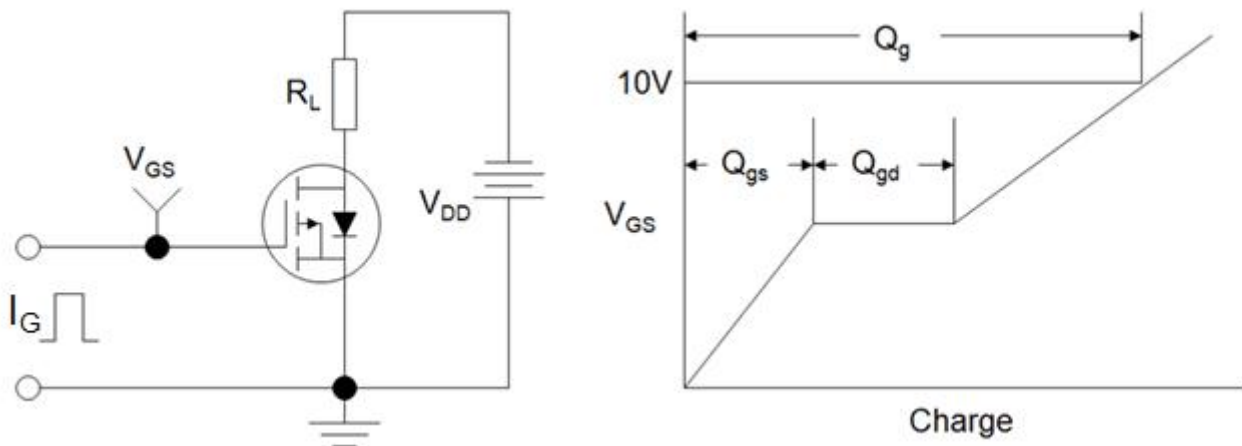
1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. EAS condition : $T_J = 25^\circ\text{C}$, $V_{DD} = -50V$, $V_{GS} = -10V$, $L = 0.5mH$, $R_g = 25\Omega$

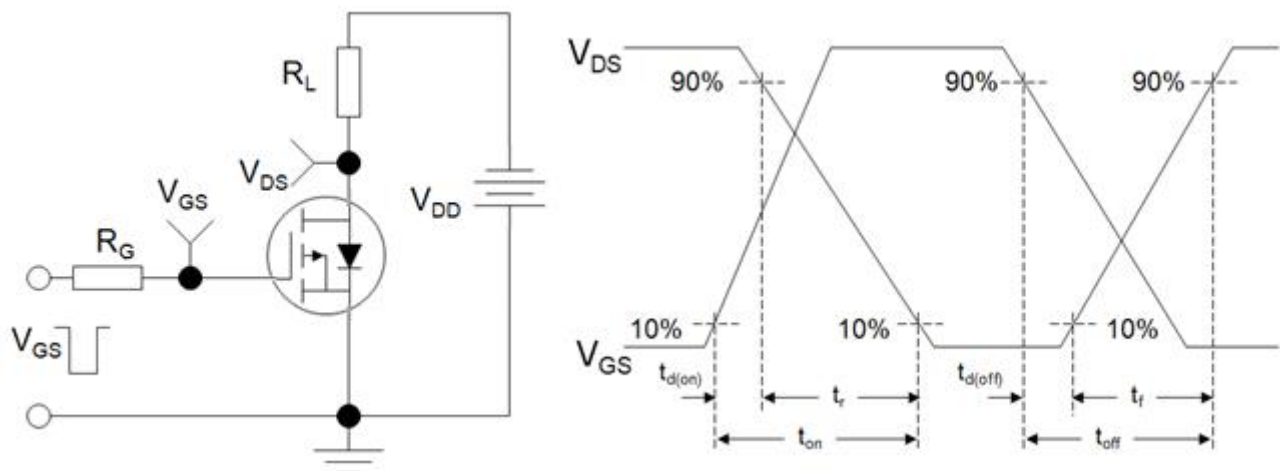
The table shows the minimum avalanche energy, which is 900mJ when the device is tested until failure

3. Identical low side and high side switch with identical R_G

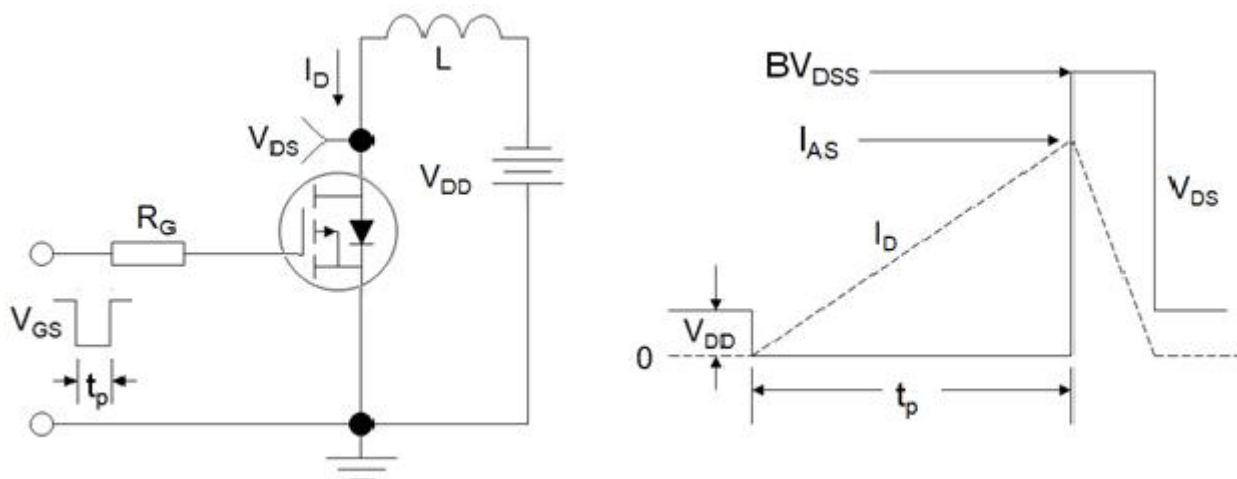
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

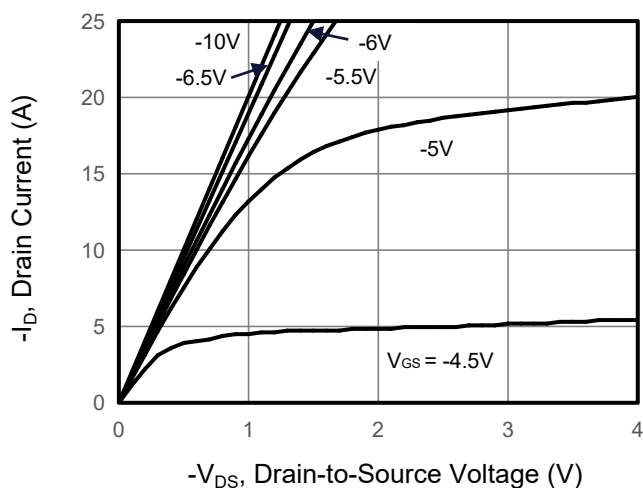


Figure 2. Transfer Characteristics

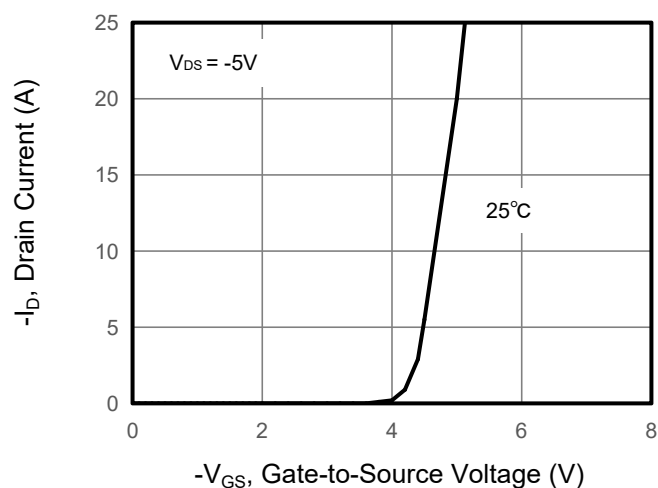


Figure 3. Drain Source On Resistance

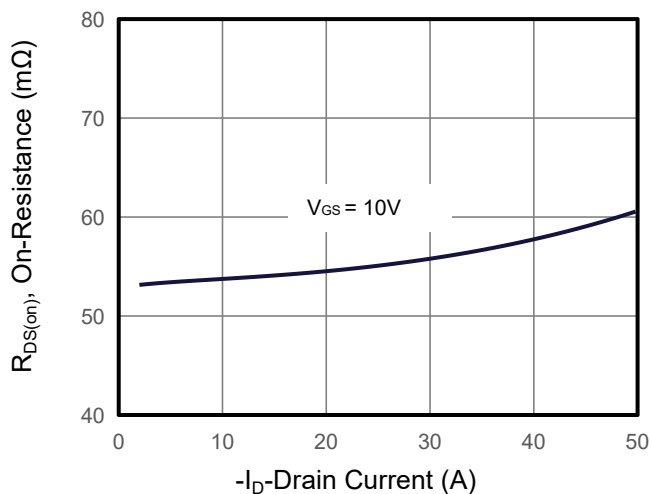


Figure 4. Gate Charge

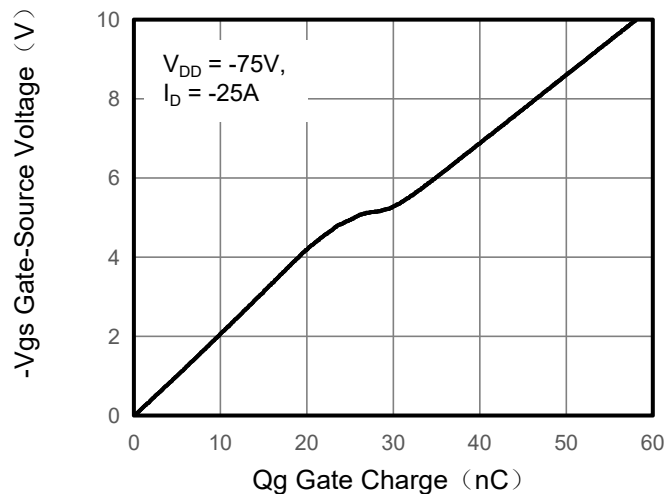


Figure 5. Capacitance

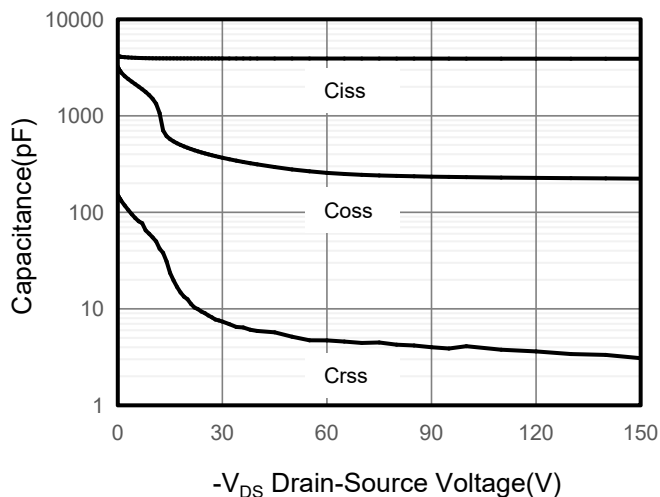
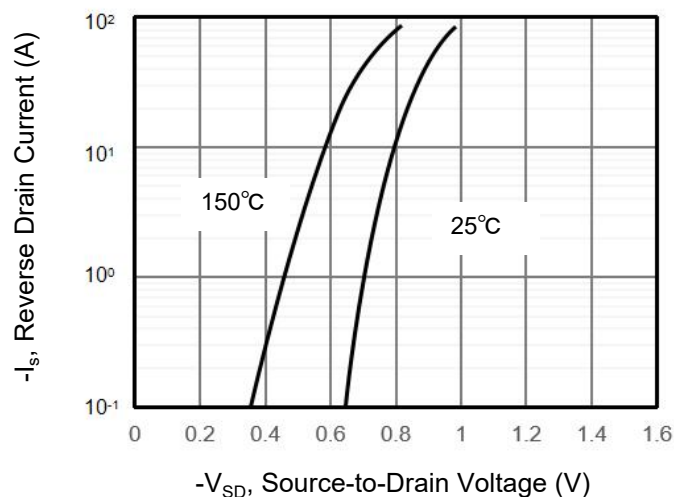


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

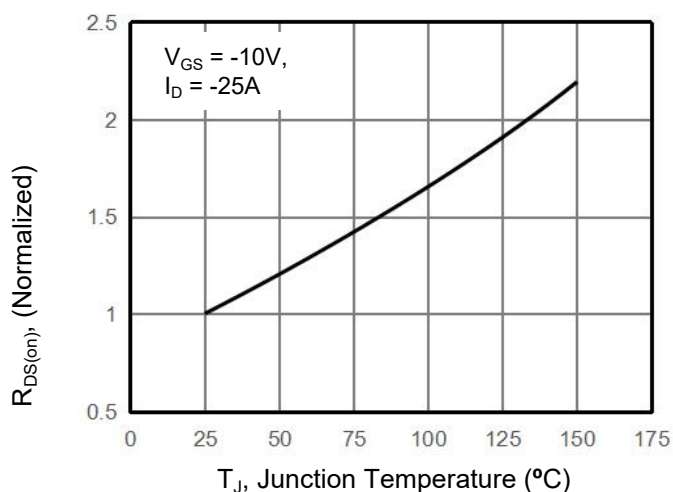


Figure 8. Safe Operation Area

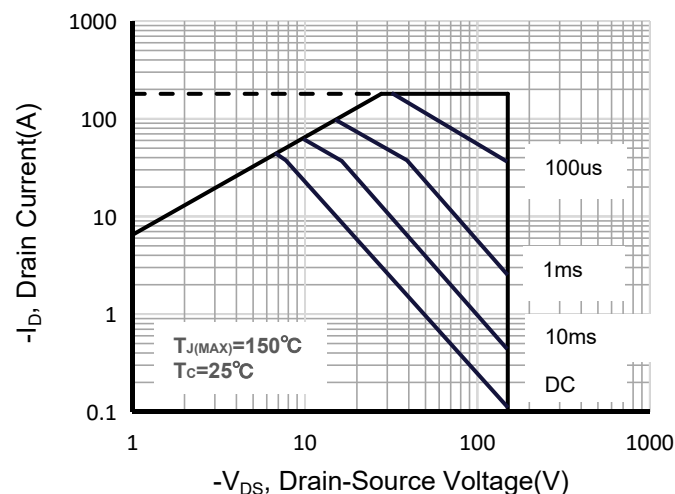


Figure 9. Maximum Continuous Drain Current vs Case Temperature

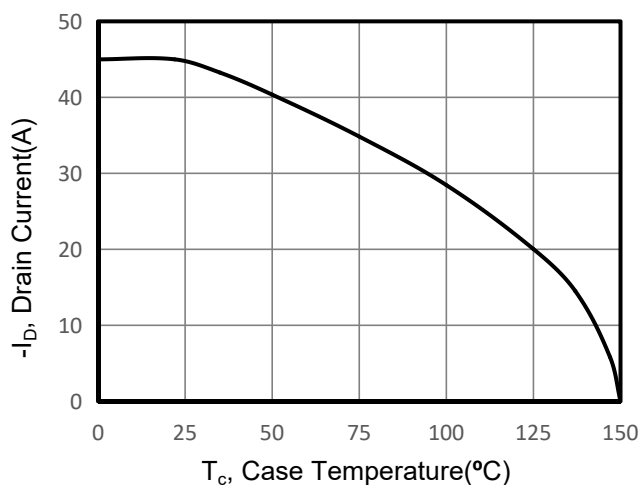
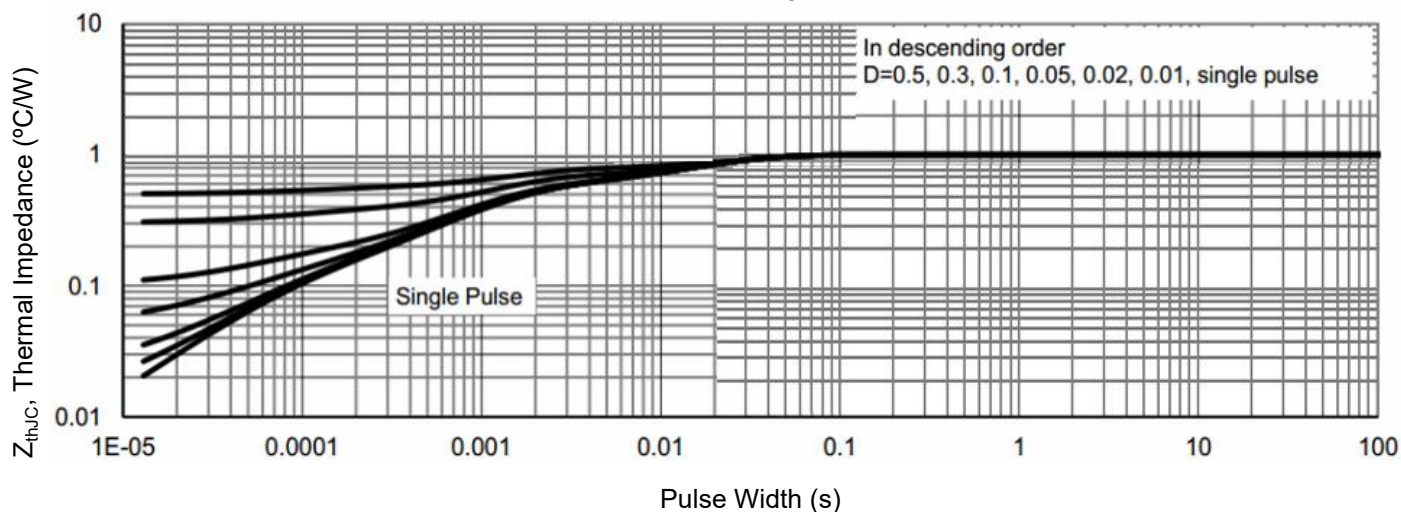
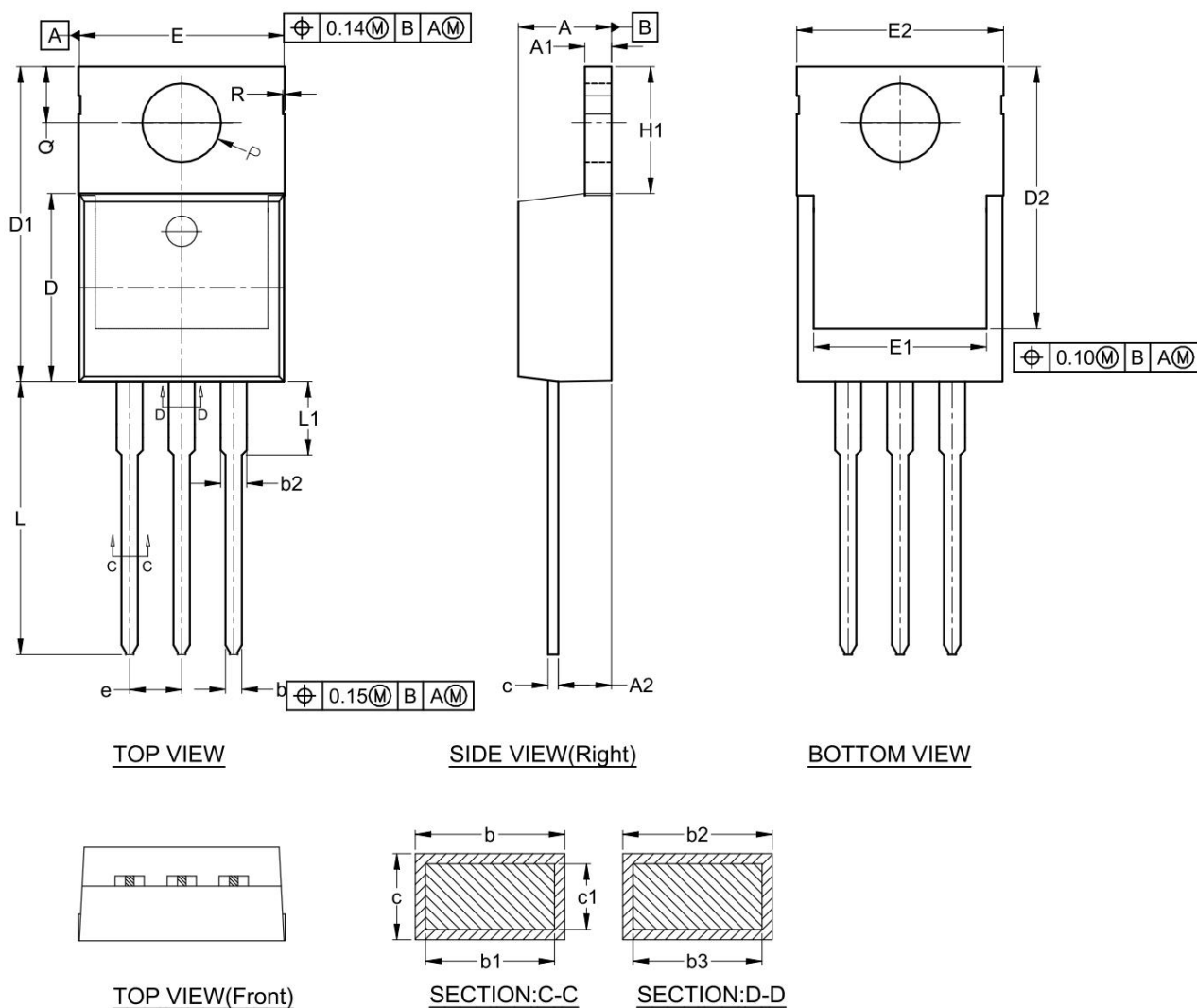


Figure 10. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



DIM SYMBOL	MIN.	NOM.	MAX.	DIM SYMBOL	MIN.	NOM.	MAX.
A	4.450	4.550	4.650	D2	12.610	12.810	13.010
A1	1.240	1.340	1.440	E	9.900	10.000	10.100
A2	2.500	2.600	2.700	E1	8.240	8.440	8.640
b	0.740	0.840	0.940	E2	9.900	10.100	10.300
b1	0.700	0.800	0.900	e	2.540 BSC.		
b2	1.210	1.310	1.410	H1	6.000	6.200	6.400
b3	1.170	1.270	1.370	L	13.140	13.340	13.540
c	0.440	0.540	0.640	L1	3.385	3.585	3.785
c1	0.400	0.500	0.600	$\emptyset P$	3.740	3.840	3.940
D	9.100	9.200	9.300	Q	2.600	2.740	2.940
D1	15.200	15.400	15.600	R	0.108 REF.		